

RECOMMEND
YJG2D7G06A



YJG95G06A

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Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250 μ E	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μ E
Gate-Body Leakage Current	I _{GSS}	V _{GS} = 20V, V _{DS} =0V			100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250 μ E	1.2	1.6	2.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D =20A		2.1	2.5	m
		V _{GS} = 4.5V, I _D =15A		2.7	3.4	
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V			1.2	V
Maximum Body-Diode Continuous Current	I _S				95	



Typical Performance Characteristics

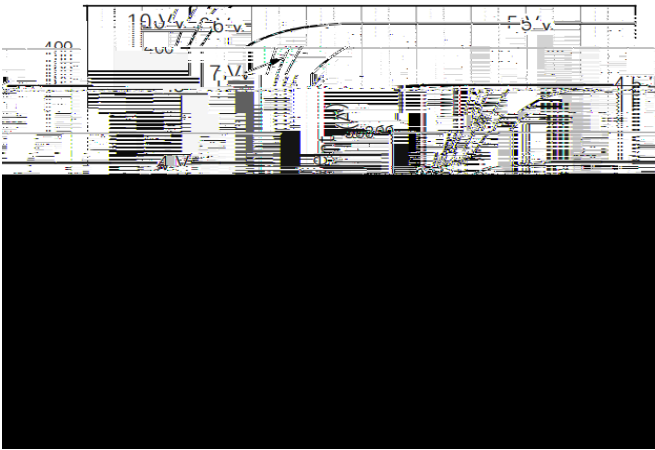


Figure1. Output Characteristics



Figure2. Transfer Characteristics

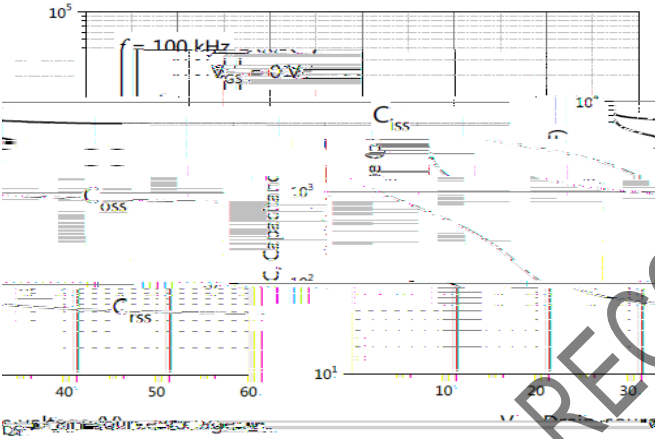


Figure3. Capacitance Characteristics

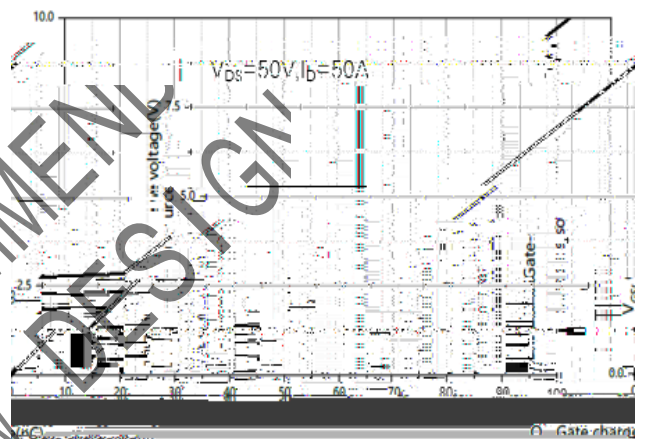


Figure4. Gate Charge

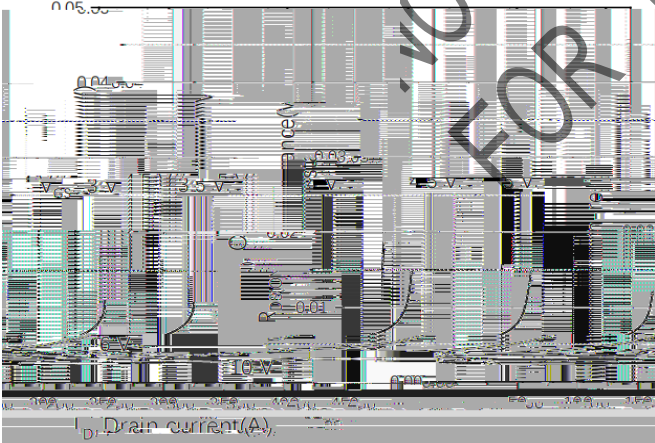


Figure5. Drain-Source on Resistance

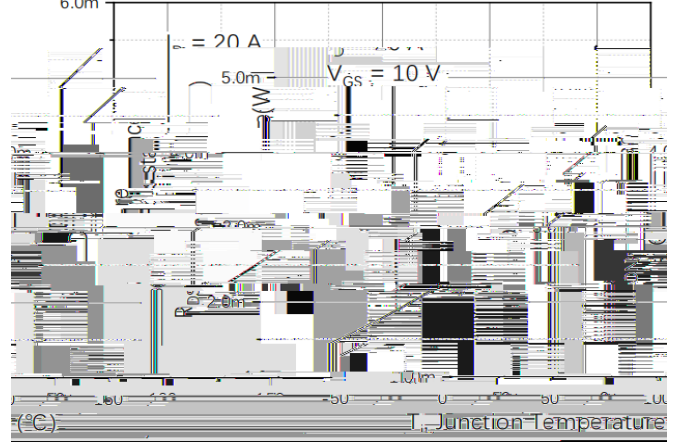


Figure6. Drain-Source on Resistance

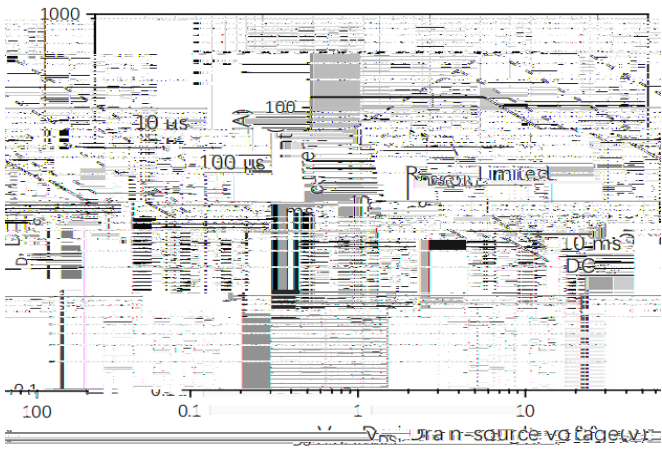


Figure 7. Safe Operation Area

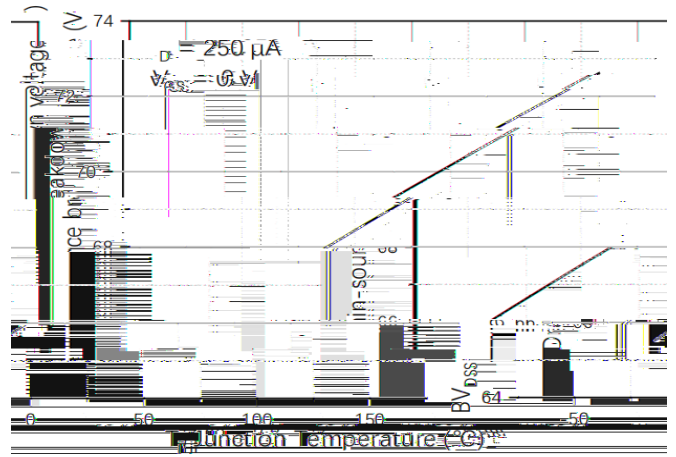


Figure 8. Drain-source breakdown voltage

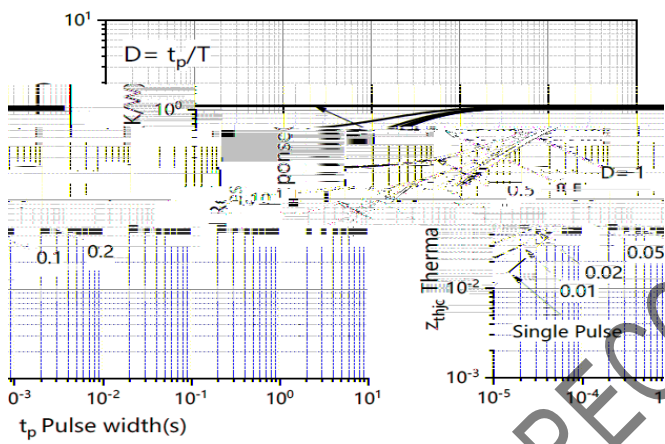


Figure 9. Transient thermal impedance

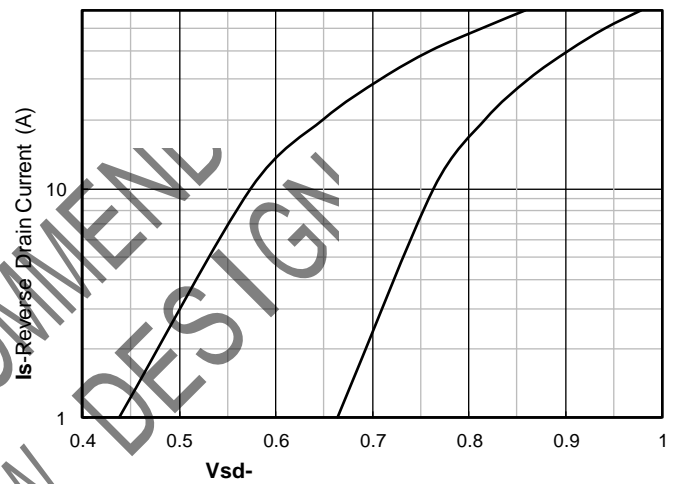


Figure 10. Forward characteristics of reverse diode

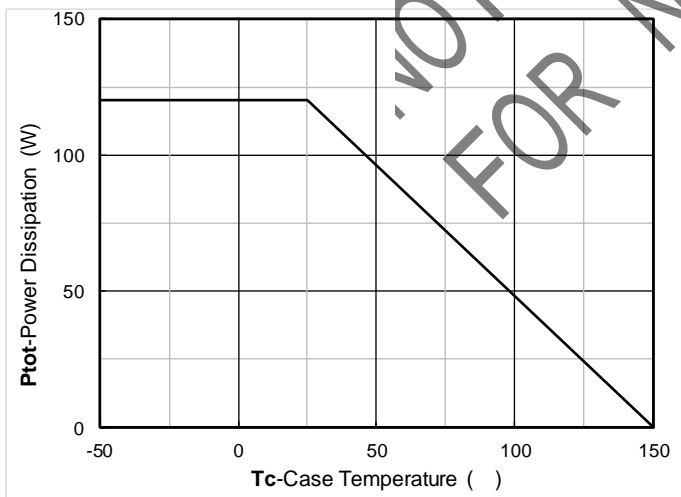


Figure 11. Power dissipation

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